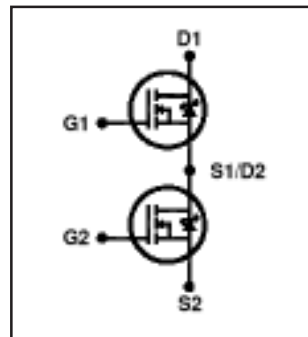


IRFI4024H-117P

Features

- Integrated half-bridge package
- Reduces the part count by half
- Facilitates better PCB layout
- Key parameters optimized for Class-D audio amplifier applications
- Low $R_{DS(ON)}$ for improved efficiency
- Low Q_g and Q_{sw} for better THD and improved efficiency
- Low Q_{rr} for better THD and lower EMI
- Can delivery up to 100W per channel into 6Ω load in full-bridge configuration amplifier
- Lead-free package

Key Parameters ⑤		
V_{DS}	55	V
$R_{DS(ON)}$ typ. @ 10V	48	mΩ
Q_g typ.	8.9	nC
Q_{sw} typ.	4.3	nC
$R_{G(int)}$ typ.	2.3	Ω
T_J max	150	°C



G1, G2	D1, D2	S1, S2
Gate	Drain	Source

Description

This Digital Audio MosFET Half-Bridge is specifically designed for Class D audio amplifier applications. It consists of two power MosFET switches connected in half-bridge configuration. The latest process is used to achieve low on-resistance per silicon area. Furthermore, Gate charge, body-diode reverse recovery, and internal Gate resistance are optimized to improve key Class D audio amplifier performance factors such as efficiency, THD and EMI. These combine to make this Half-Bridge a highly efficient, robust and reliable device for Class D audio amplifier applications.

Absolute Maximum Ratings ⑤

	Parameter	Max.	Units
V_{DS}	Drain-to-Source Voltage	55	V
V_{GS}	Gate-to-Source Voltage	±20	
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	11	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	6.9	
I_{DM}	Pulsed Drain Current ①	44	
P_D @ $T_C = 25^\circ\text{C}$	Power Dissipation	14	W
P_D @ $T_C = 100^\circ\text{C}$	Power Dissipation	5.4	
	Linear Derating Factor	0.11	W/°C
E_{AS}	Single Pulse Avalanche Energy②	7.4	mJ
T_J	Operating Junction and	-55 to +150	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

Thermal Resistance ⑤

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ④	—	9.21	°C/W
$R_{\theta JA}$	Junction-to-Ambient (free air)	—	65	

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified) ⑤

	Parameter	Min.	Typ.	Max.	Units	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	55	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	54	—	mV/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	48	60	mΩ	$V_{GS} = 10V, I_D = 7.7A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 25\mu A$
$\Delta V_{GS(th)}/\Delta T_J$	Gate Threshold Voltage Coefficient	—	-9.17	—	mV/°C	
I_{DSS}	Drain-to-Source Leakage Current	—	—	20	μA	$V_{DS} = 55V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 55V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -20V$
g_{fs}	Forward Transconductance	6.5	—	—	S	$V_{DS} = 25V, I_D = 7.7A$
Q_g	Total Gate Charge	—	8.9	13	nC	$V_{DS} = 44V$ $V_{GS} = 10V$ $I_D = 7.7A$ See Fig. 6 and 15
Q_{gs1}	Pre-V _{th} Gate-to-Source Charge	—	1.6	—		
Q_{gs2}	Post-V _{th} Gate-to-Source Charge	—	0.77	—		
Q_{gd}	Gate-to-Drain Charge	—	3.5	—		
Q_{godr}	Gate Charge Overdrive	—	3.0	—		
Q_{sw}	Switch Charge ($Q_{gs2} + Q_{gd}$)	—	4.3	—		
$R_{G(int)}$	Internal Gate Resistance	—	2.3	—	Ω	
$t_{d(on)}$	Turn-On Delay Time	—	5.9	—	ns	$V_{DD} = 28V, V_{GS} = 10V$ ③ $I_D = 7.7A$ $R_G = 2.5\Omega$
t_r	Rise Time	—	2.0	—		
$t_{d(off)}$	Turn-Off Delay Time	—	13	—		
t_f	Fall Time	—	3.4	—		
C_{iss}	Input Capacitance	—	320	—	pF	$V_{GS} = 0V$ $V_{DS} = 50V$ $f = 1.0\text{MHz}$, See Fig. 5
C_{oss}	Output Capacitance	—	47	—		
C_{rss}	Reverse Transfer Capacitance	—	31	—		
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		

Diode Characteristics ⑤

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S @ T_C = 25^\circ\text{C}$	Continuous Source Current (Body Diode)	—	—	11	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	44		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 7.7A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	17	26	ns	$T_J = 25^\circ\text{C}, I_F = 7.7A$
Q_{rr}	Reverse Recovery Charge	—	11	17	nC	$di/dt = 100A/\mu s$ ③

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting $T_J = 25^\circ\text{C}$, $L = 0.25\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 7.7A$.
- ③ Pulse width $\leq 400\mu s$; duty cycle $\leq 2\%$.
- ④ R_{θ} is measured at T_J of approximately 90°C .
- ⑤ Specifications refer to single MosFET.

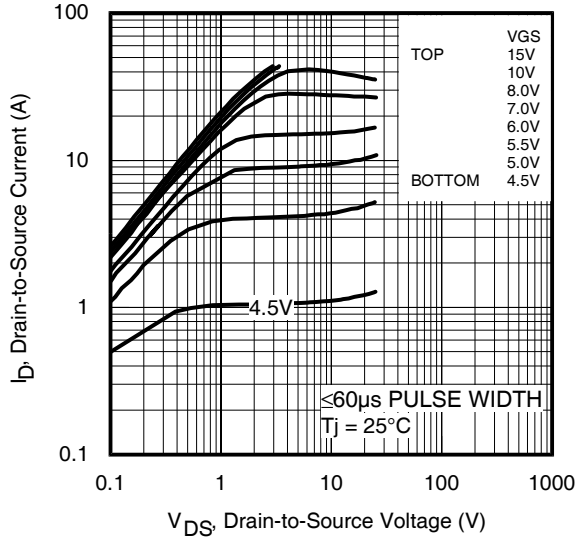


Fig 1. Typical Output Characteristics

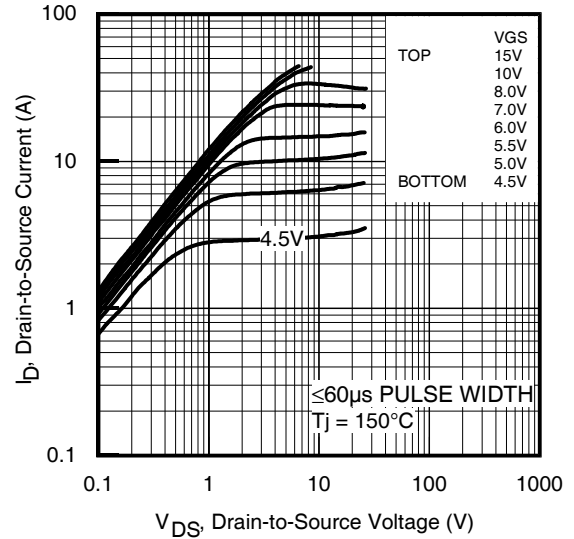


Fig 2. Typical Output Characteristics

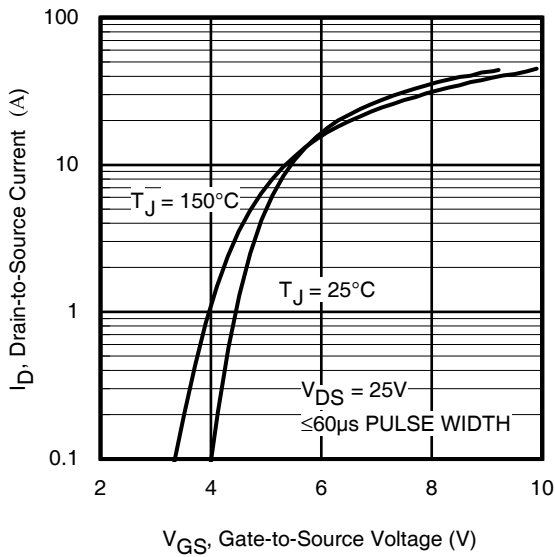


Fig 3. Typical Transfer Characteristics

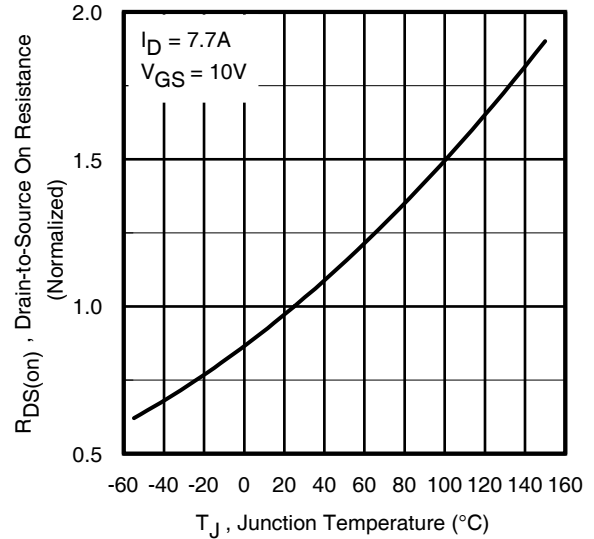


Fig 4. Normalized On-Resistance vs. Temperature

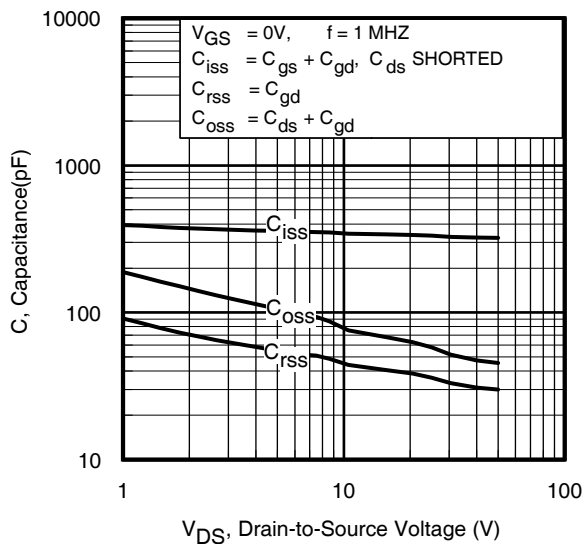


Fig 5. Typical Capacitance vs. Drain-to-Source Voltage
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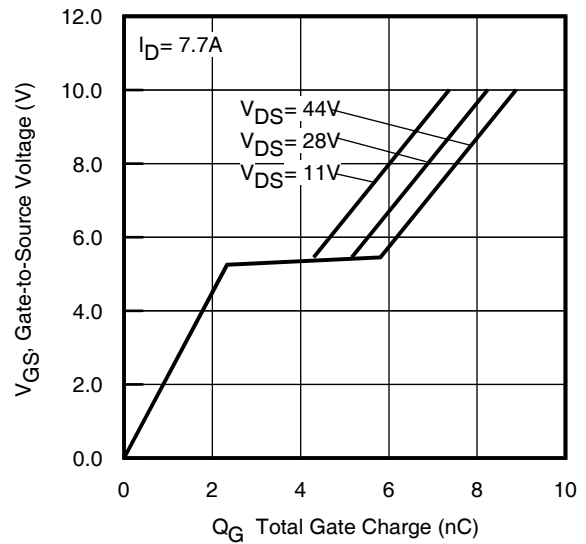


Fig 6. Typical Gate Charge vs. Gate-to-Source Voltage

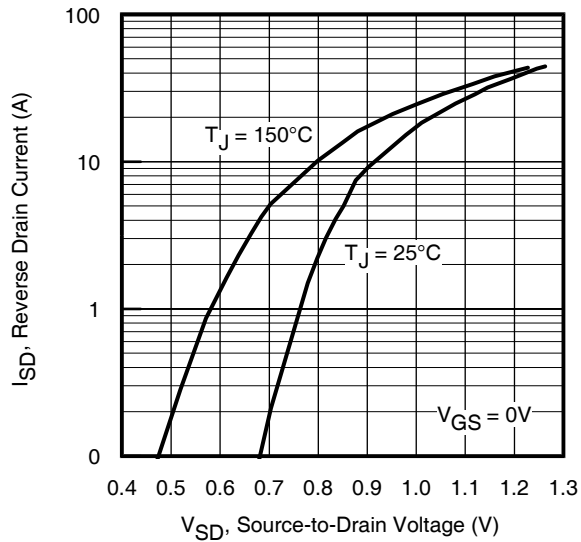


Fig 7. Typical Source-Drain Diode Forward Voltage

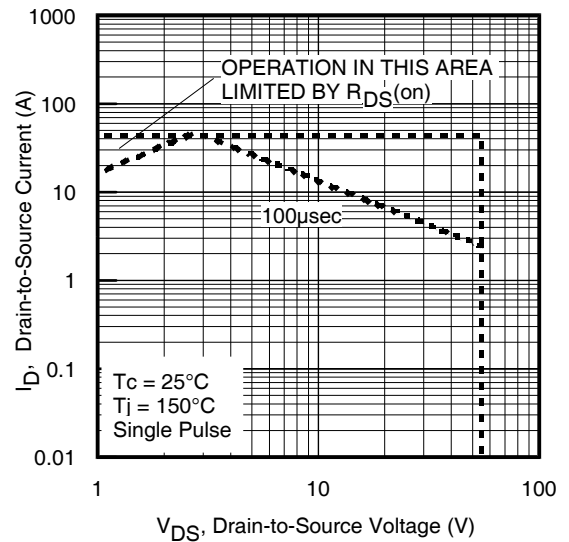


Fig 8. Maximum Safe Operating Area

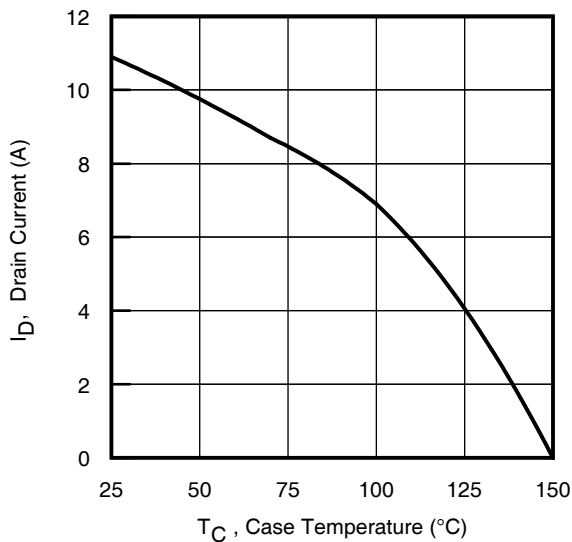


Fig 9. Maximum Drain Current vs. Case Temperature

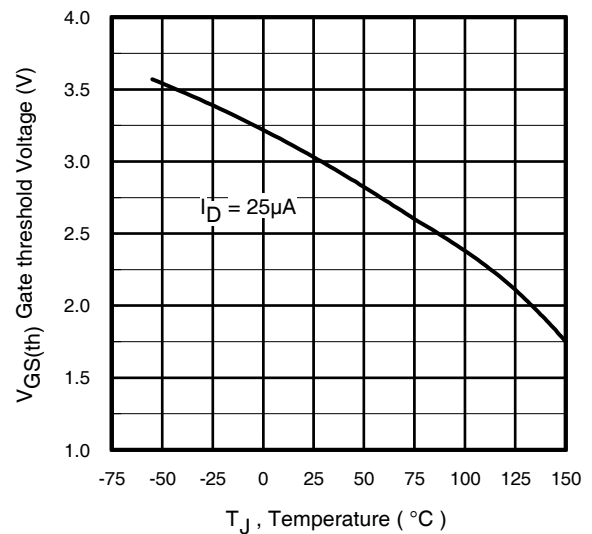


Fig 10. Threshold Voltage vs. Temperature

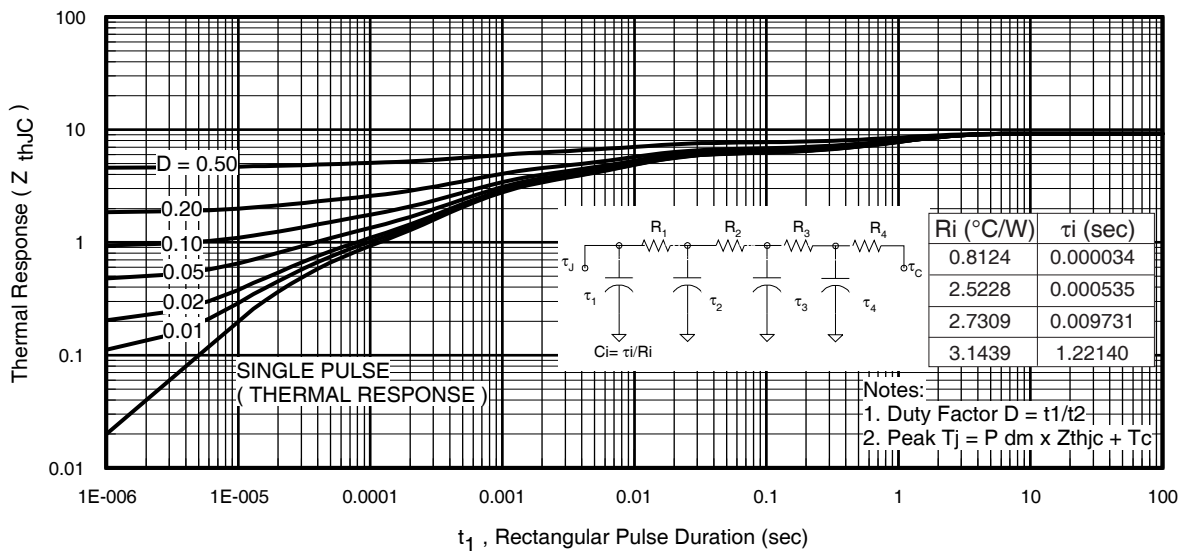


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

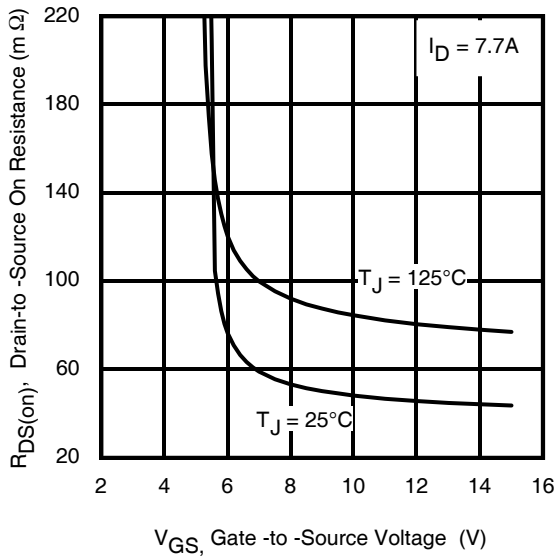


Fig 12. On-Resistance vs. Gate Voltage

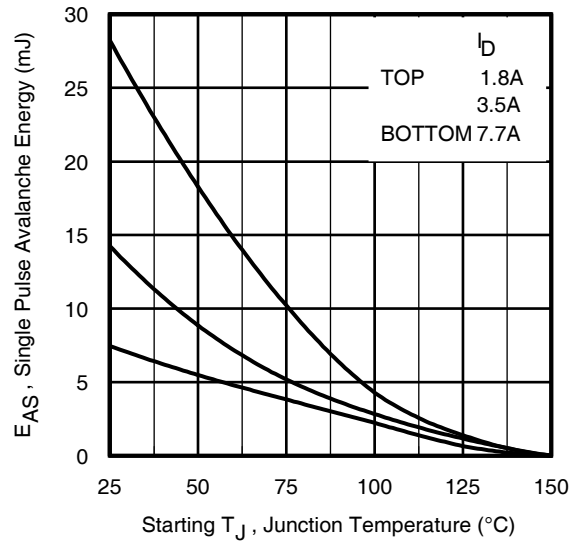


Fig 13a. Maximum Avalanche Energy vs. Drain Current

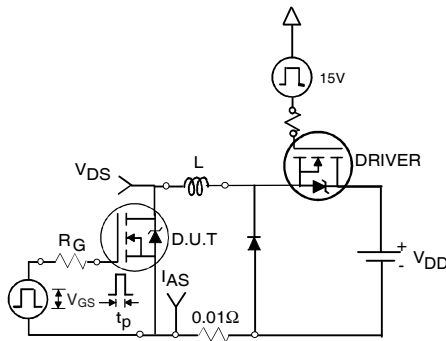


Fig 13b. Unclamped Inductive Test Circuit

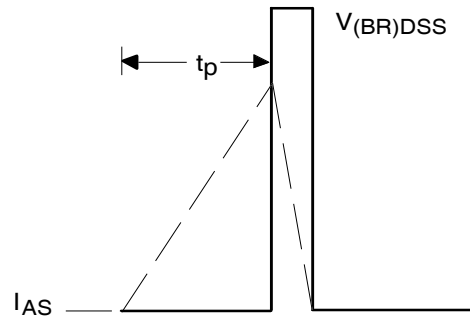


Fig 13c. Unclamped Inductive Waveforms

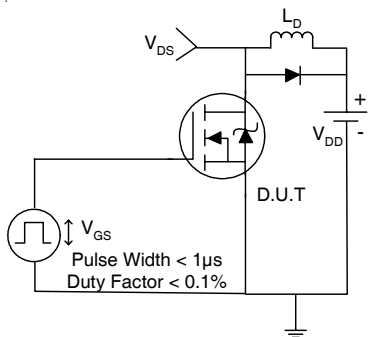


Fig 14a. Switching Time Test Circuit

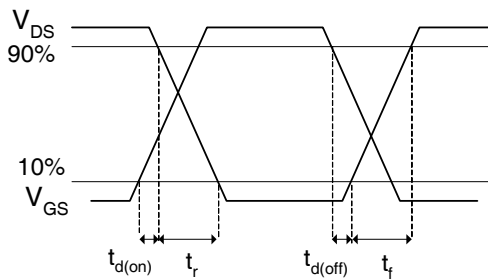


Fig 14b. Switching Time Waveforms

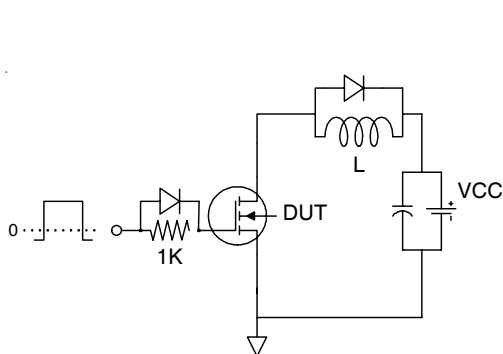


Fig 15a. Gate Charge Test Circuit

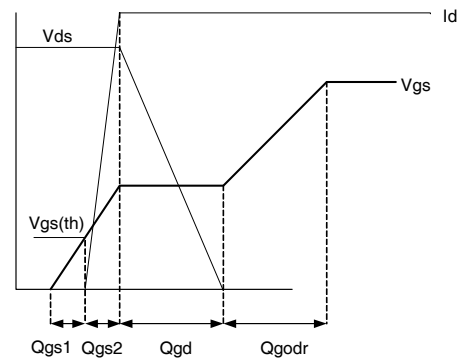


Fig 15b Gate Charge Waveform

Note: For the most current drawings please refer to the IR website at:
<http://www.irf.com/package/>